Silicon NPN Power Transistors 2SC1368

DESCRIPTION

·With TO-126 package
·Low collector saturation voltage

APPLICATIONS

·For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

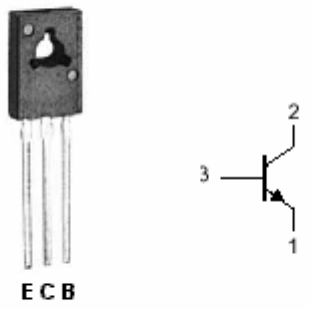

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	25	V
V_{CEO}	Collector-emitter voltage	Open base	25	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
P_C	Collector power dissipation	T_C=25□	8	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA; I_B=0	25			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=50μA; I_E=0	25			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=50μA; I_B=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=1.5A; I_B=0.15A			0.8	V
I_{CBO}	Collector cut-off current	V_{CB}=25V; I_E=0			1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			1.0	μA
h_{FE}	DC current gain	I_C=0.5A ; V_{CE}=2V	60		320	
f_T	Transition frequency	I_C=0.5A ; V_{CE}=5V		180		MHz

PACKAGE OUTLINE

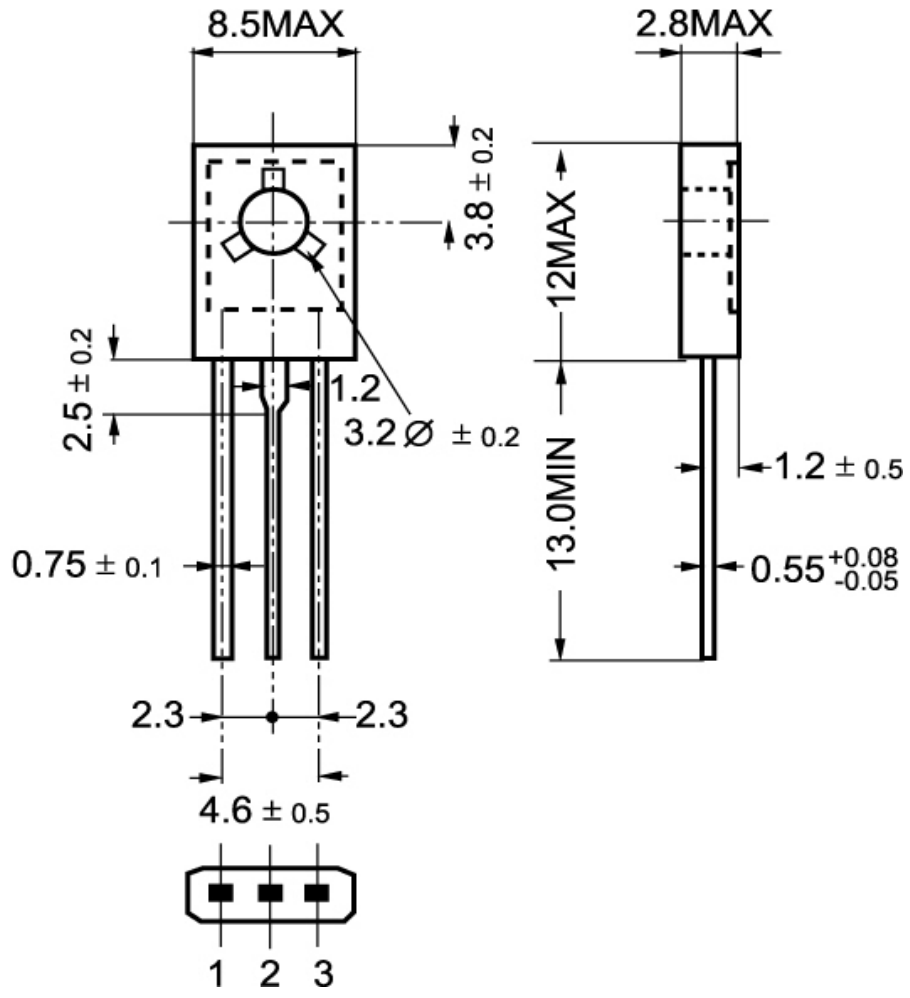

Fig.2 Outline dimensions